

Features

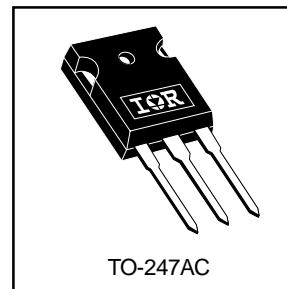
- Fast: Optimized for medium operating frequencies (1-5 kHz in hard switching, >20 kHz in resonant mode).
- Generation 4 IGBT design provides tighter parameter distribution and higher efficiency than Generation 3
- Industry standard TO-247AC package



$V_{CES} = 600V$
 $V_{CE(on)} \text{ typ.} = 1.59V$
 @ $V_{GE} = 15V, I_C = 17A$

Benefits

- Generation 4 IGBT's offer highest efficiency available
- IGBT's optimized for specified application conditions
- Designed to be a "drop-in" replacement for equivalent industry-standard Generation 3 IR IGBT's



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Breakdown Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	31	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	17	
I_{CM}	Pulsed Collector Current ①	120	
I_{LM}	Clamped Inductive Load Current ②	120	
V_{GE}	Gate-to-Emitter Voltage	± 20	V
E_{ARV}	Reverse Voltage Avalanche Energy ③	10	mJ
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	100	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	42	
T_J	Operating Junction and Storage Temperature Range	-55 to + 150	°C
T_{STG}			
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.2	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	40	
Wt	Weight	6 (0.21)	—	g (oz)

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)CES}	Collector-to-Emitter Breakdown Voltage	600	—	—	V	V _{GE} = 0V, I _C = 250μA
V _{(BR)ECS}	Emitter-to-Collector Breakdown Voltage ④	18	—	—	V	V _{GE} = 0V, I _C = 1.0A
ΔV _{(BR)CES} /ΔT _J	Temperature Coeff. of Breakdown Voltage	—	0.69	—	V/°C	V _{GE} = 0V, I _C = 1.0mA
V _{CE(ON)}	Collector-to-Emitter Saturation Voltage	—	1.59	1.8	V	I _C = 17A, V _{GE} = 15V See Fig.2, 5
		—	1.99	—		
		—	1.7	—		
V _{GE(th)}	Gate Threshold Voltage	3.0	—	6.0		I _C = 17A, T _J = 150°C
ΔV _{GE(th)} /ΔT _J	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/°C	V _{CE} = V _{GE} , I _C = 250μA
g _{fe}	Forward Transconductance ⑤	6.1	10	—	S	V _{CE} = 100V, I _C = 17A
I _{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	V _{GE} = 0V, V _{CE} = 600V
		—	—	2.0		V _{GE} = 0V, V _{CE} = 10V, T _J = 25°C
		—	—	1000		V _{GE} = 0V, V _{CE} = 600V, T _J = 150°C
I _{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V _{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q _g	Total Gate Charge (turn-on)	—	51	77	nC	I _C = 17A V _{CC} = 400V, V _{GE} = 15V See Fig. 8
Q _{ge}	Gate - Emitter Charge (turn-on)	—	7.9	12		
Q _{gc}	Gate - Collector Charge (turn-on)	—	19	28		
t _{d(on)}	Turn-On Delay Time	—	21	—	ns	T _J = 25°C I _C = 17A, V _{CC} = 480V V _{GE} = 15V, R _G = 23Ω Energy losses include "tail" See Fig. 10, 11, 13, 14
t _r	Rise Time	—	15	—		
t _{d(off)}	Turn-Off Delay Time	—	200	300		
t _f	Fall Time	—	180	270		
E _{on}	Turn-On Switching Loss	—	0.23	—	mJ	See Fig. 10, 11, 13, 14
E _{off}	Turn-Off Switching Loss	—	1.18	—		
E _{ts}	Total Switching Loss	—	1.41	2.0		
t _{d(on)}	Turn-On Delay Time	—	20	—	ns	T _J = 150°C, I _C = 17A, V _{CC} = 480V V _{GE} = 15V, R _G = 23Ω Energy losses include "tail" See Fig. 13, 14
t _r	Rise Time	—	16	—		
t _{d(off)}	Turn-Off Delay Time	—	290	—		
t _f	Fall Time	—	350	—		
E _{ts}	Total Switching Loss	—	2.5	—	mJ	
L _E	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package
C _{ies}	Input Capacitance	—	1100	—	pF	V _{GE} = 0V V _{CC} = 30V, f = 1.0MHz See Fig. 7
C _{oes}	Output Capacitance	—	74	—		
C _{res}	Reverse Transfer Capacitance	—	14	—		

Notes:

- ① Repetitive rating; V_{GE} = 20V, pulse width limited by max. junction temperature. (See fig. 13b)
- ② V_{CC} = 80%(V_{CES}), V_{GE} = 20V, L = 10μH, R_G = 23Ω, (See fig. 13a)
- ③ Repetitive rating; pulse width limited by maximum junction temperature.
- ④ Pulse width ≤ 80μs; duty factor ≤ 0.1%.
- ⑤ Pulse width 5.0μs, single shot.

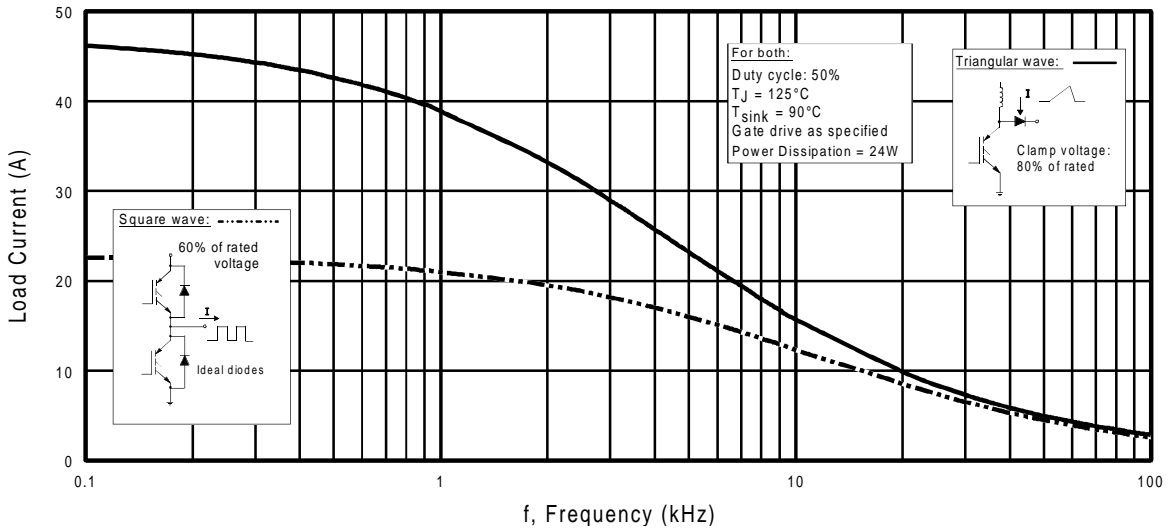


Fig. 1 - Typical Load Current vs. Frequency
(For square wave, $I = I_{RMS}$ of fundamental; for triangular wave, $I = I_{PK}$)

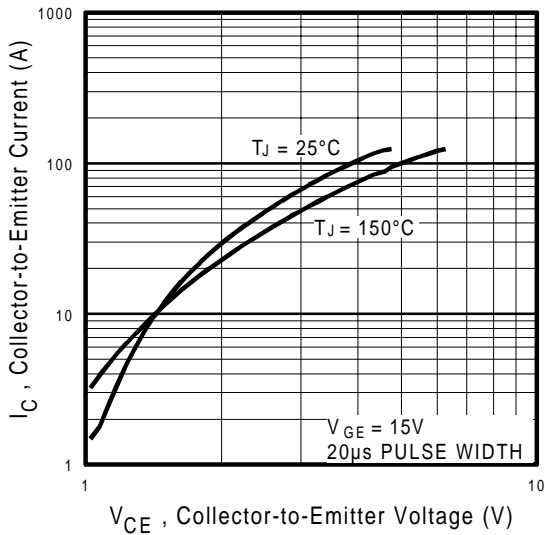


Fig. 2 - Typical Output Characteristics

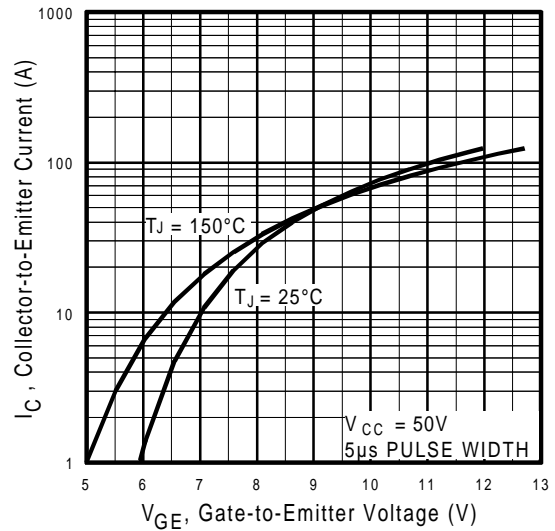


Fig. 3 - Typical Transfer Characteristics

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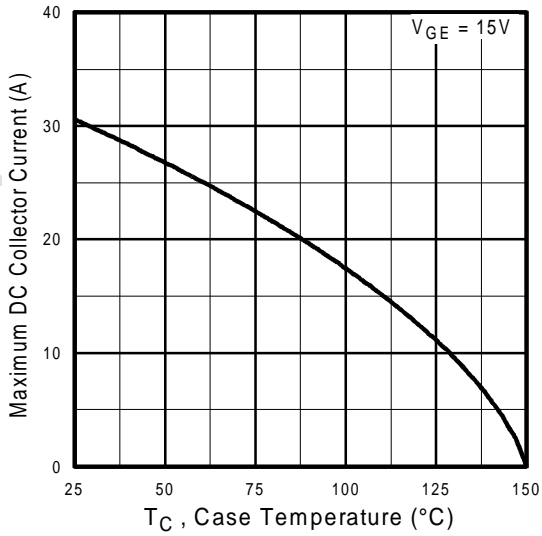


Fig. 4 - Maximum Collector Current vs. Case Temperature

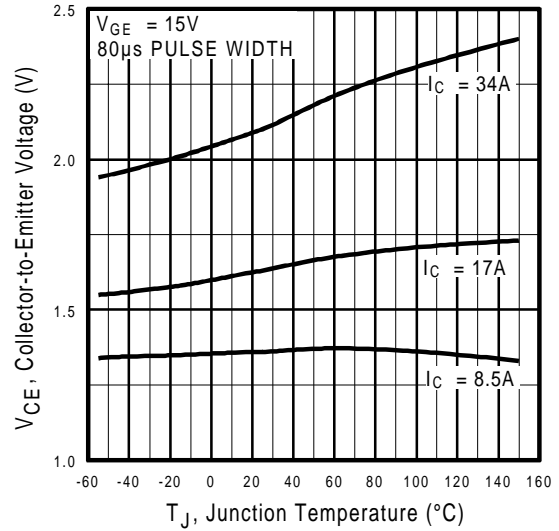


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

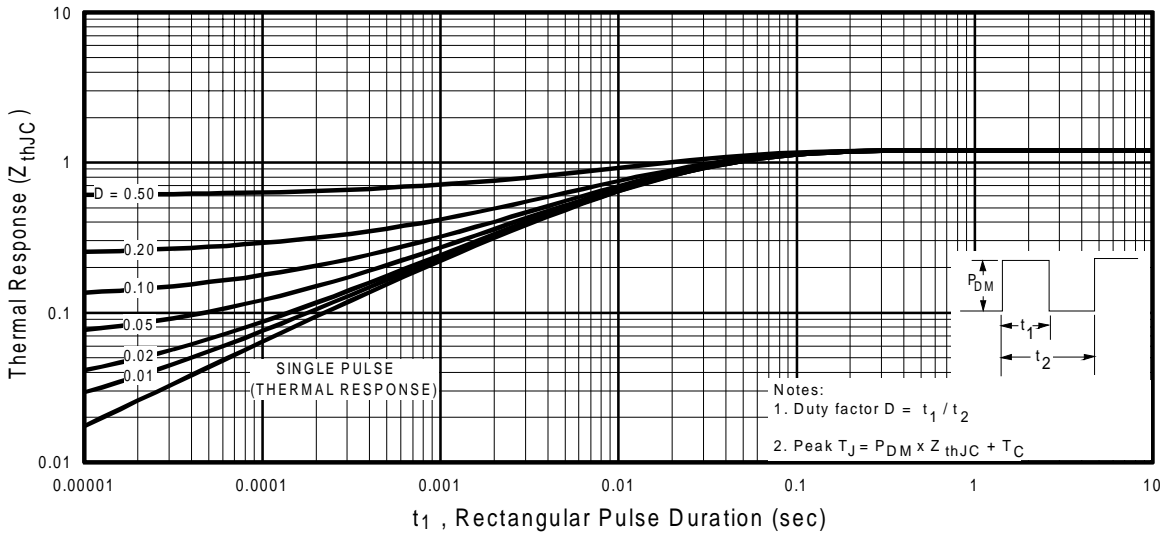


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

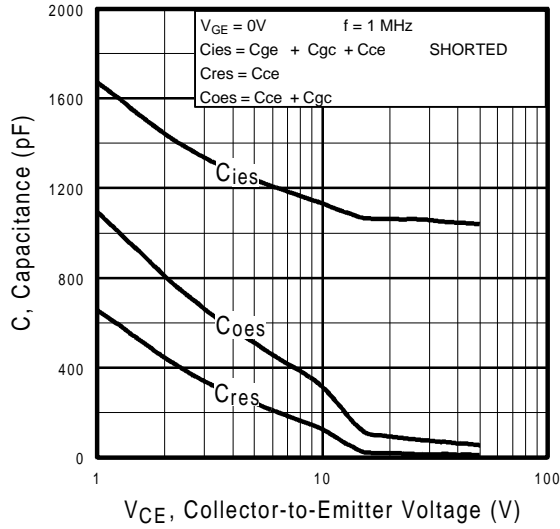


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

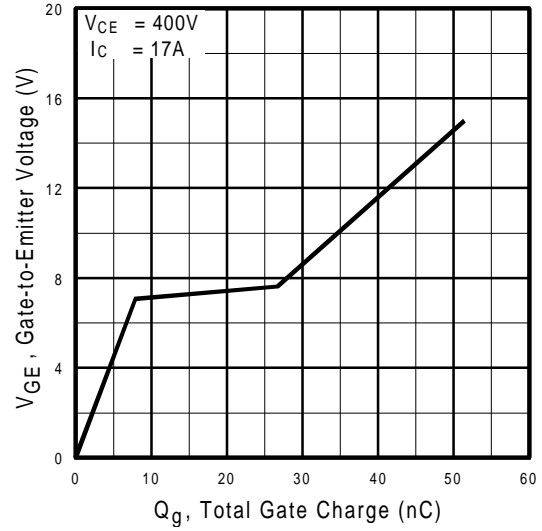


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

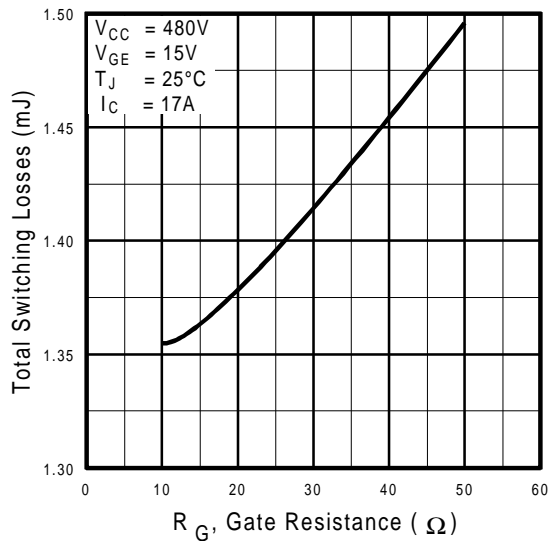


Fig. 9 - Typical Switching Losses vs. Gate Resistance

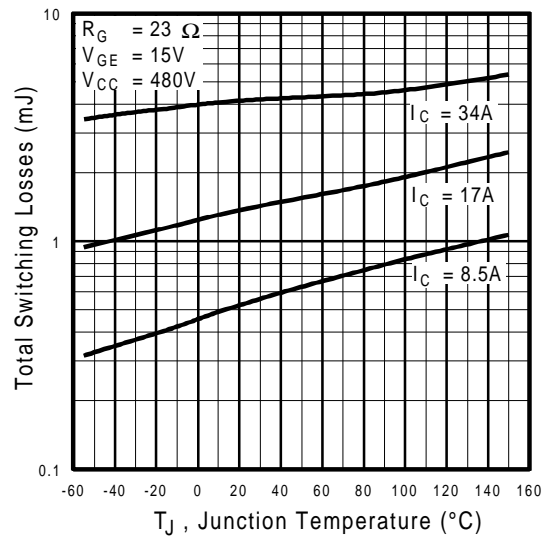


Fig. 10 - Typical Switching Losses vs. Junction Temperature

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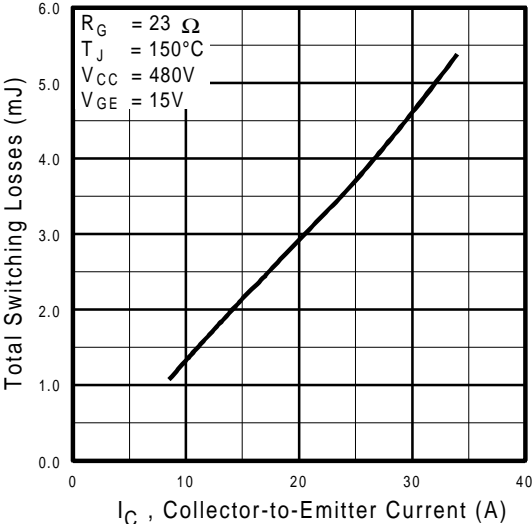


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

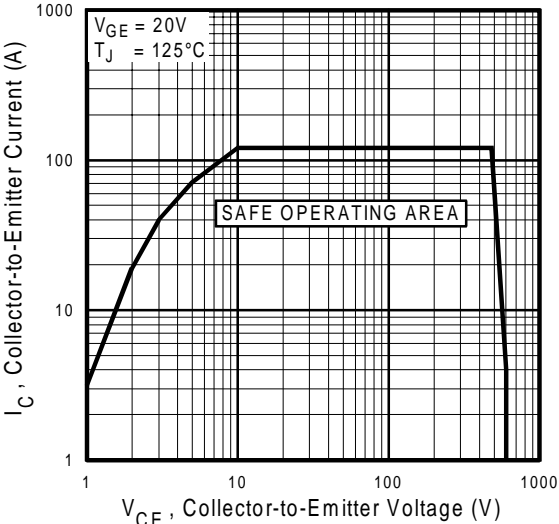


Fig. 12 - Turn-Off SOA



* Driver same type as D.U.T.; $V_c = 80\%$ of $V_{ce(max)}$
 * Note: Due to the 50V power supply, pulse width and inductor will increase to obtain rated I_d .

Fig. 13a - Clamped Inductive Load Test Circuit

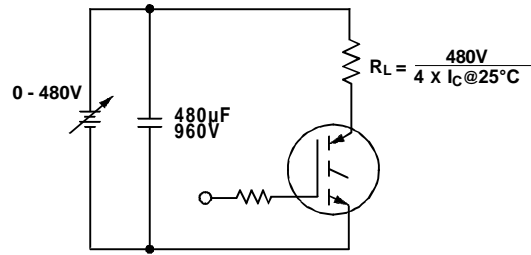


Fig. 13b - Pulsed Collector Current Test Circuit



Fig. 14a - Switching Loss Test Circuit

* Driver same type as D.U.T., $V_C = 480V$

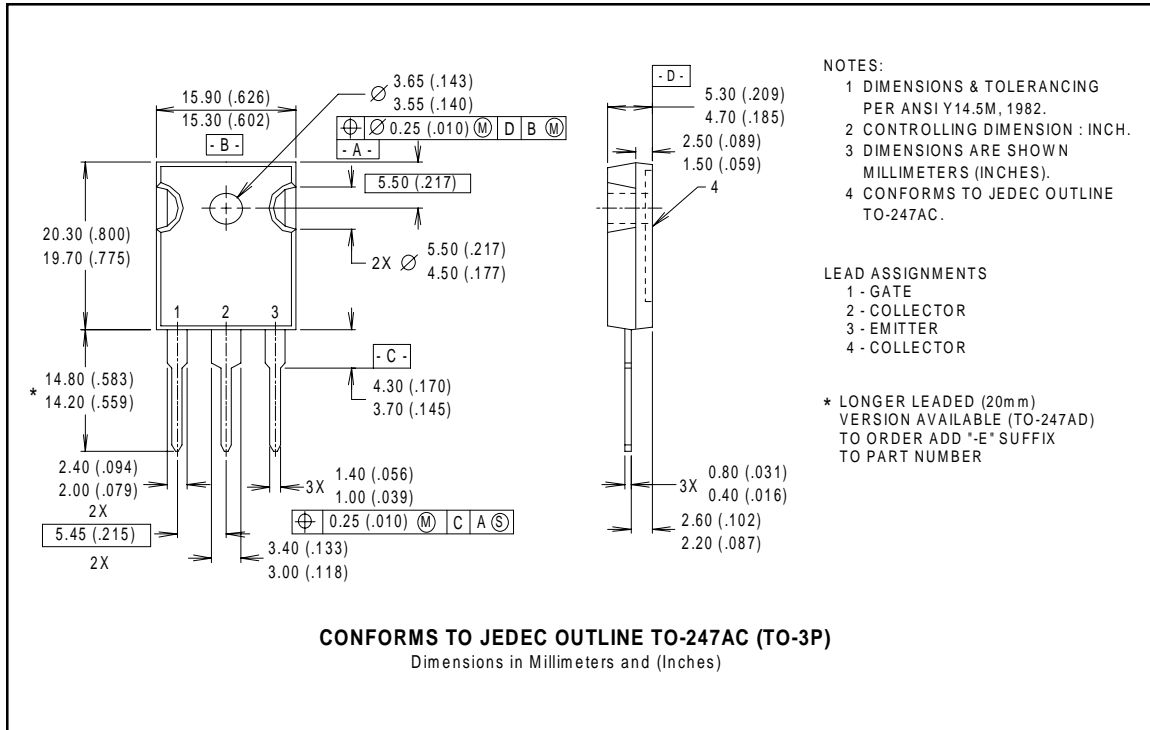


Fig. 14b - Switching Loss Waveforms

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Case Outline and Dimensions — TO-247AC



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IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903

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